

H5N5015P

Silicon N Channel MOS FET
High Speed Power Switching

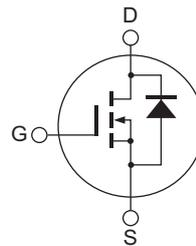
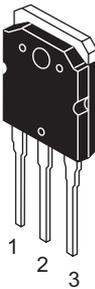
REJ03G1117-0100
(Previous: ADE-208-1522)
Rev.1.00
Sep 07, 2005

Features

- Low on-resistance
- Low leakage current
- High speed switching
- Low gate charge
- Built-in fast recovery diode

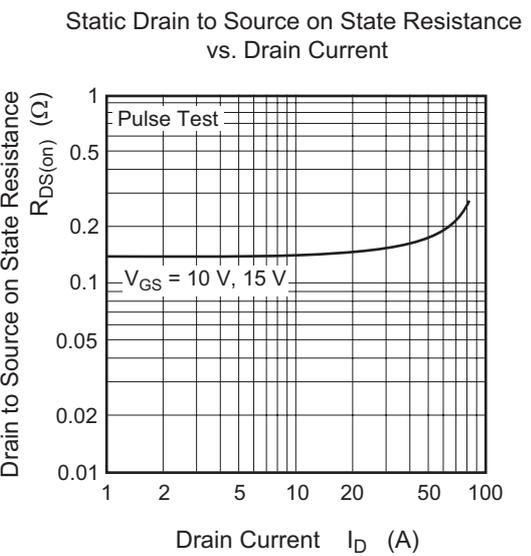
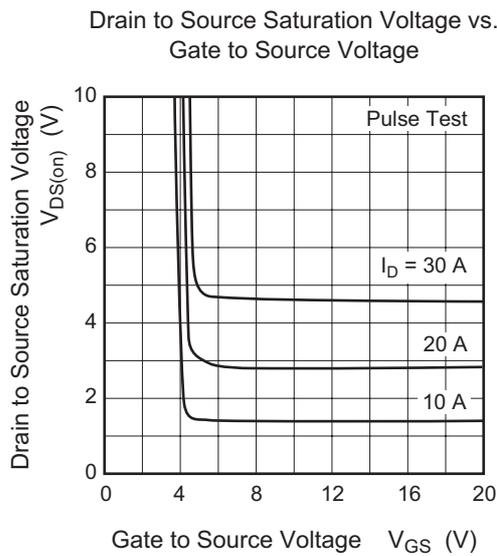
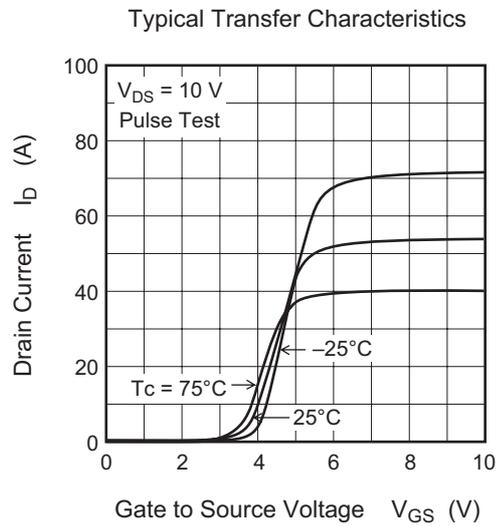
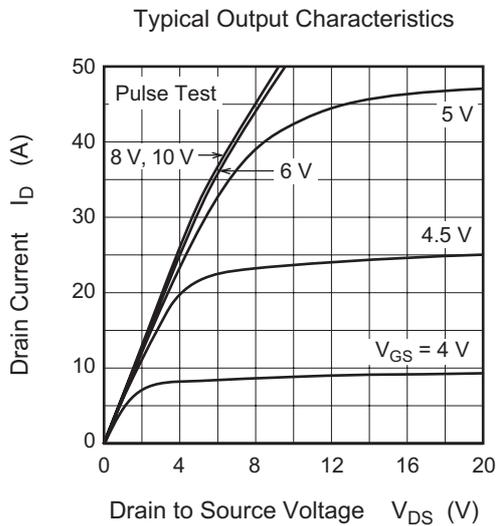
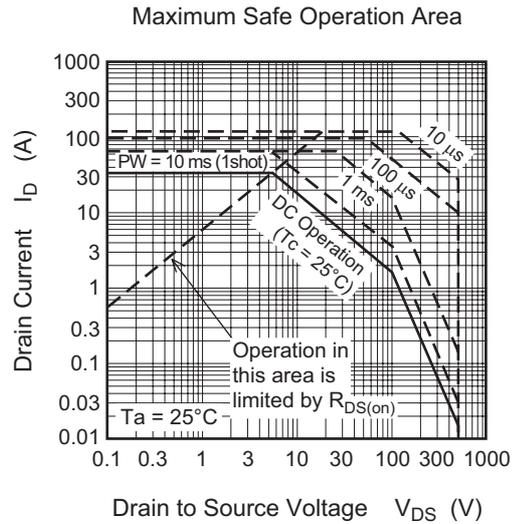
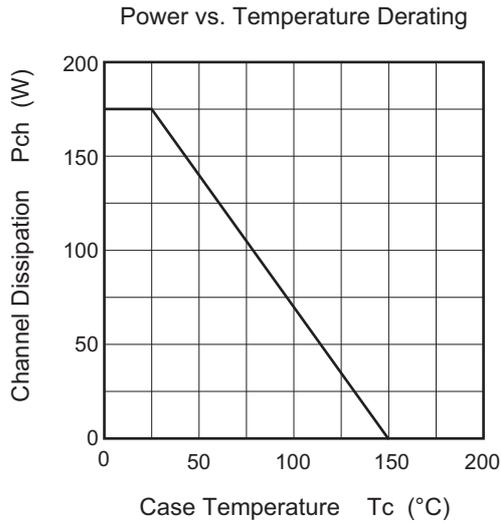
Outline

RENESAS Package code: PRSS0004ZE-A
(Package name: TO-3P)

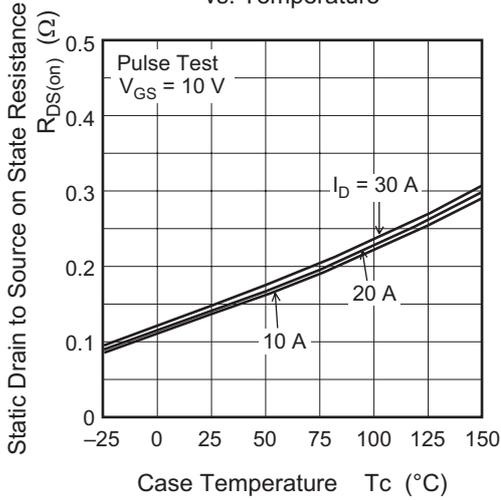


1. Gate
2. Drain (Flange)
3. Source

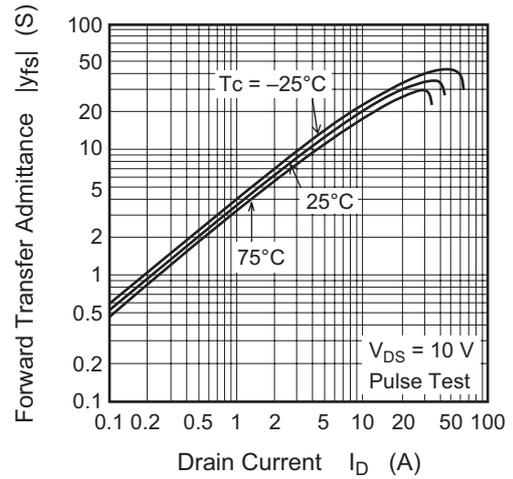
Main Characteristics



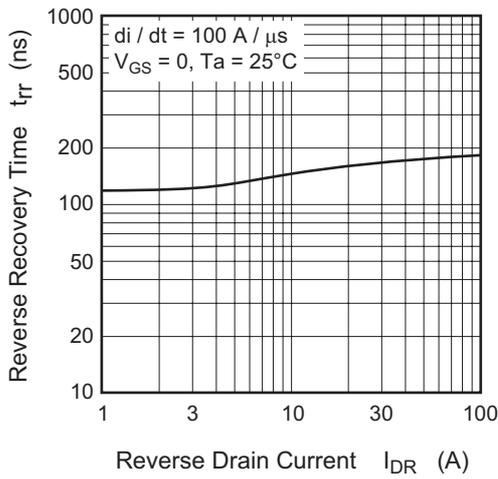
Static Drain to Source on State Resistance vs. Temperature



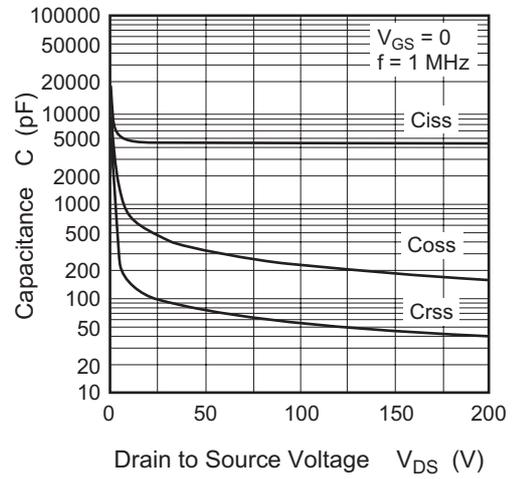
Forward Transfer Admittance vs. Drain Current



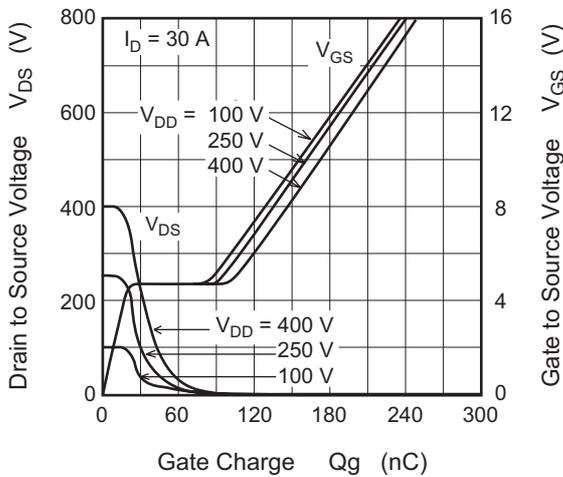
Body-Drain Diode Reverse Recovery Time



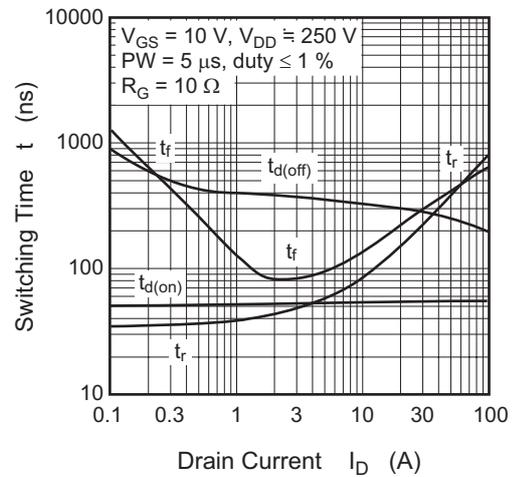
Typical Capacitance vs. Drain to Source Voltage



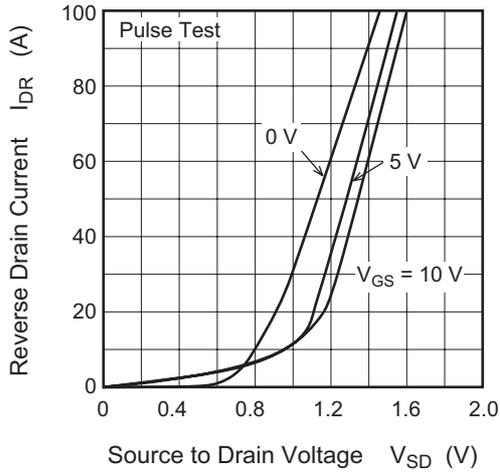
Dynamic Input Characteristics



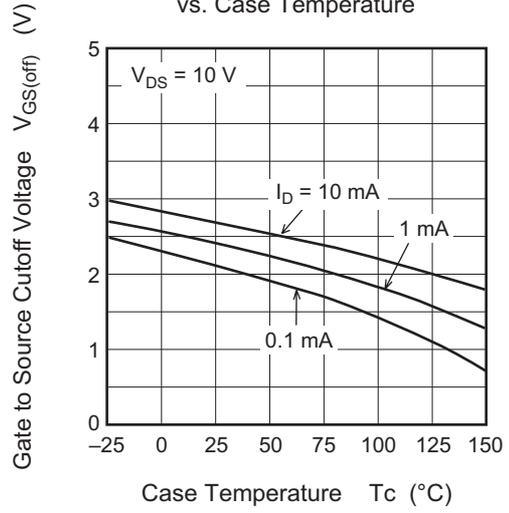
Switching Characteristics



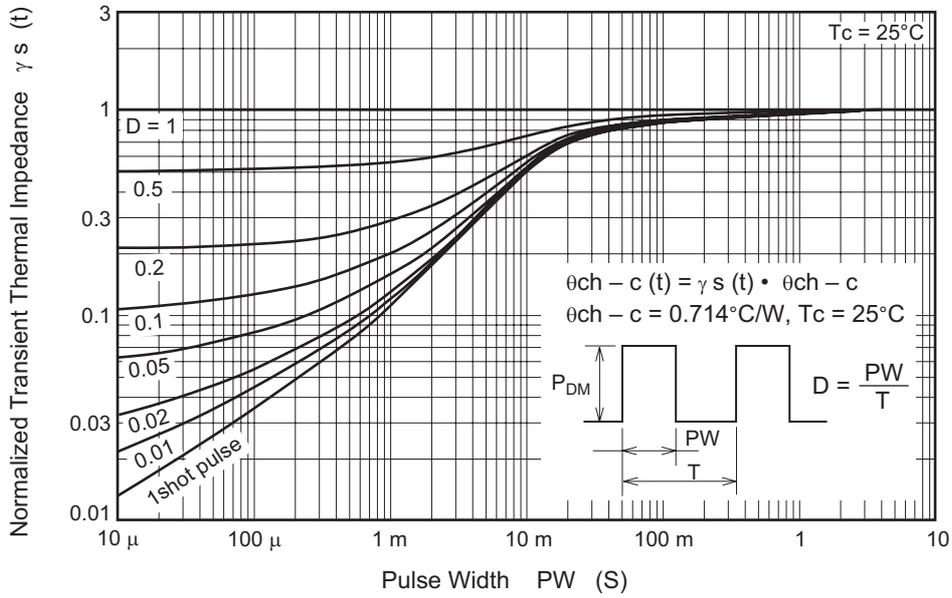
Reverse Drain Current vs. Source to Drain Voltage



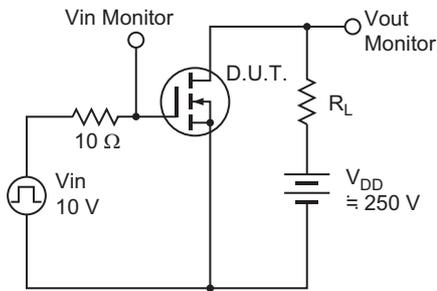
Gate to Source Cutoff Voltage vs. Case Temperature



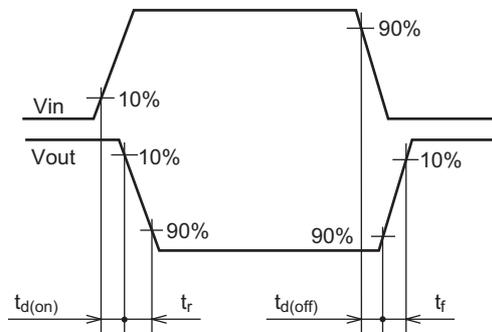
Normalized Transient Thermal Impedance vs. Pulse Width



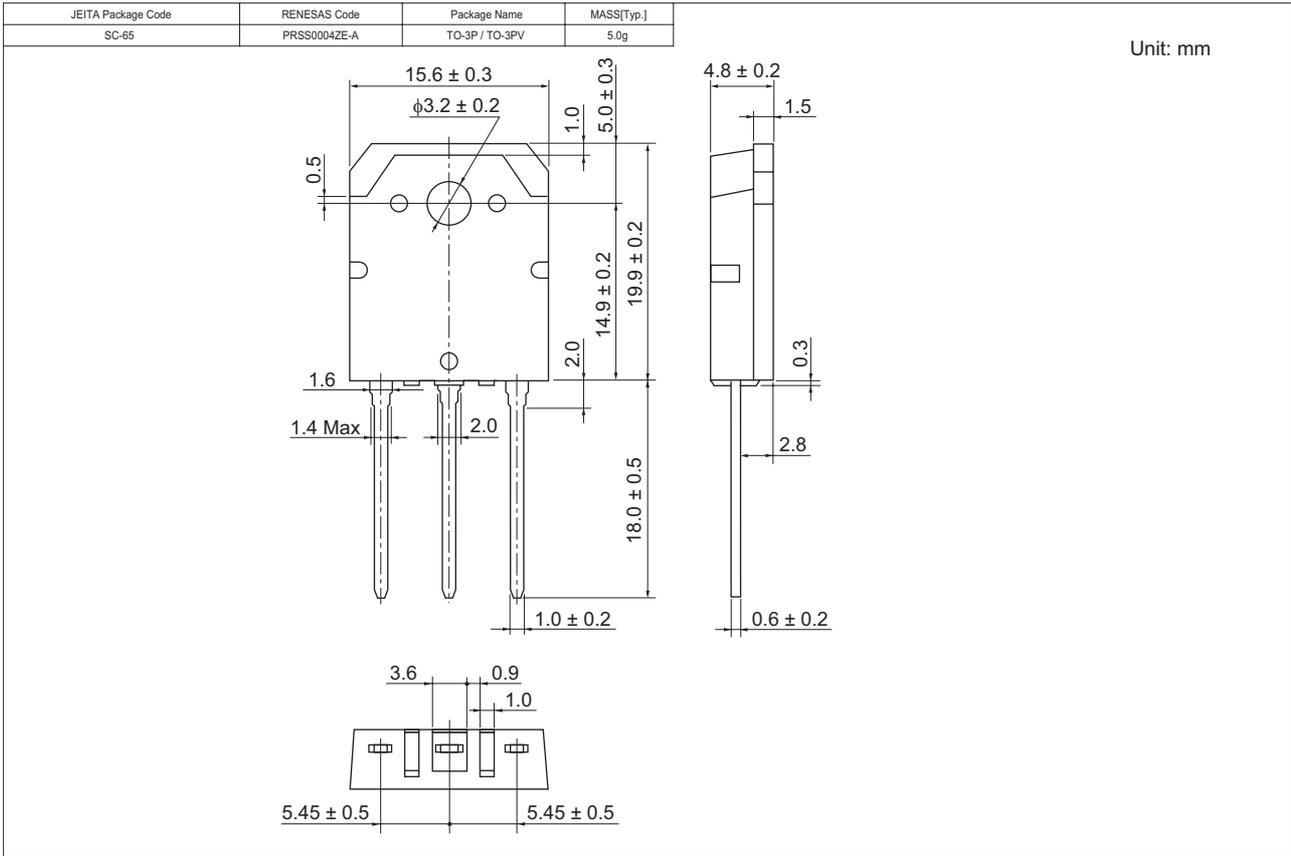
Switching Time Test Circuit



Waveform



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
H5N5015P-E	360 pcs	Box (Tube)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

